
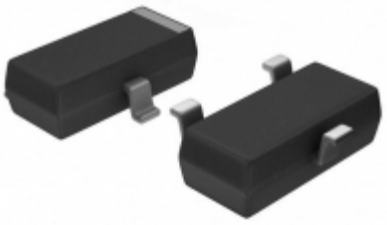
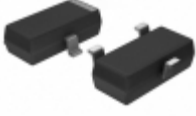



	<p>SI2351DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2351DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 2.8A SOT23-3</p> <p>Datenblätter:  SI2351DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 159163 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2351DS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 2.8A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	159163 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1W (Ta), 2.1W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.8A (Tc)
Rds On (Max) @ Id, Vgs	115 mOhm @ 2.4A, 4.5V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	5.1nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	250pF @ 10V
Verpackung	Original-Reel®

















SI2351DS-T1-GE3 ist neu im Original, Suche SI2351DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2351DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2351DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2365EDS-M Original</p>	 <p>SI2356DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 4.3A SOT-23</p>	 <p>SI2350DS VISHAY SI2350DS VISHAY</p>	 <p>SI2351DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.8A SOT23-3</p>
 <p>SI2351DS-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 2.8A SOT23-3</p>	 <p>SI2351DS Vishay Precision Group SI2351DS VISHAY</p>	 <p>SI2356DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 4.3A SOT-23</p>	 <p>SI2351DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.8A SOT23-3</p>

heiße Teile

Mehr

 SI2338DS-T1-GE3	 SI2338DS-T1-GE3	 SI2341DS	 SI2341DS-T1-E3	 SI2341DS-T1-E3
 SI2341DS-T1-GE3	 SI2341DS-T1-GE3	 SI2342DS-T1-E3	 SI2342DS-T1-GE3	 SI2342DS-T1-GE3
 SI2343ADS-T1-GE3	 SI2343CDS	 SI2343CDS-T1-E3	 SI2343CDS-T1-GE3	 SI2343CDS-T1-GE3
 SI2343DS-T1-E3	 SI2343DS-T1-E3	 SI2343DS-T1-GE3	 SI2343DS-T1-GE3	 SI2344DS-E3
 SI2347DS-T1-GE3	 SI2347DS-T1-GE3	 SI2351DS-T1-E3	 SI2351DS-T1-E3	 SI2351DS-T1-GE3
 SI2356DS-T1-GE3	 SI2356DS-T1-GE3	 SI2365EDS	 SI2365EDS-T1-GE3	 SI2365EDS-T1-GE3
 SI2366DS-T1-E3	 SI2366DS-T1-GE	 SI2366DS-T1-GE3	 SI2366DS-T1-GE3	 SI2367DS-T1-E3
 SI2367DS-T1-GE3	 SI2367DS-T1-GE3	 SI2369DS-T1-GE3	 SI2369DS-T1-GE3	 SI2371EDS-T1-GE3
 SI2371EDS-T1-GE3	 SI2372DS-T1-E3	 SI2372DS-T1-GE3	 SI2372DS-T1-GE3	 SI2374DS-T1-GE3
 SI2374DS-T1-GE3	 SI2377DS-T1-GE3	 SI2377EDS	 SI2377EDS-T1-E3	 SI2377EDS-T1-GE3

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